# HRF502A

# Silicon Schottky Barrier Diode for Rectifying

# **HITACHI**

ADE-208-245C(Z) Rev 3 Sep. 1997

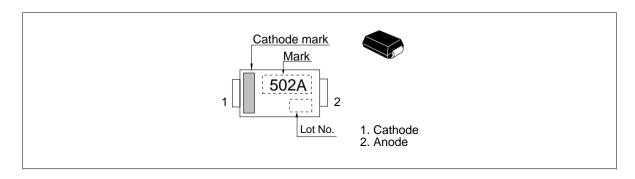
#### Features

- Low forward voltage drop and suitable for high effifiency rectifying.
- DO-214 is suitable for high density surface mounting and high speed assembly.

### **Ordering Information**

Type No.	Laser Mark	Package Code
HRF502A	502A	DO-214

#### **Outline**





# HRF502A

# **Absolute Maximum Ratings (Ta = 25^{\circ}C)**

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub> *1	20	V
Average rectified current	I <sub>o</sub> *1	5	A
Non-Repetitive peak forward surge current	I <sub>FSM</sub> *2	100	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40 to +125	°C

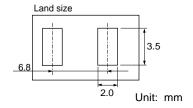
Note: 1. See from Fig.4 to Fig.7

Note: 2. 10msec half sine wave 1 pulse

## **Electrical Characteristics (Ta = 25^{\circ}C)**

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V <sub>F</sub>	_	_	0.40	V	I <sub>F</sub> = 5A
Reverse current	I <sub>R</sub>	_	_	1.0	mA	V <sub>R</sub> = 20V
ESD-Capability	_	250	_	_	V	C=200pF , R=0 $\Omega$ , Both forward and reverse direction 1 pulse.
Thermal resistance	Rth(j-a)	_	90	_	°C/W	Glass epoxy board *1
	Rth(j-c)	_	42	_	_	Tc=25°C

Note: 1. Glass epoxy board



### **Main Characteristic**

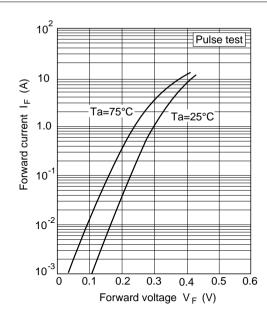


Fig.1 Forward current Vs. Forward voltage

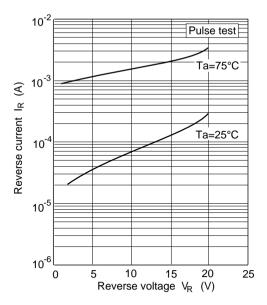


Fig.2 Reverse current Vs. Reverse voltage

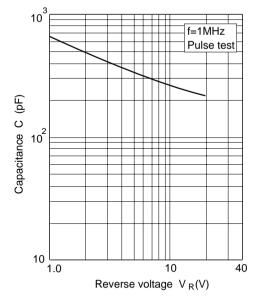


Fig.3 Capacitance Vs. Reverse voltage

# HRF502A

### **Main Characteristic**

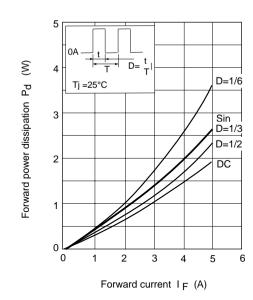


Fig.4 Forward p ower dissipation Vs. Forward current

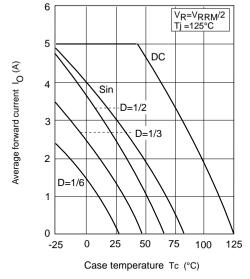


Fig.6 Average forward current Vs. Case temperature

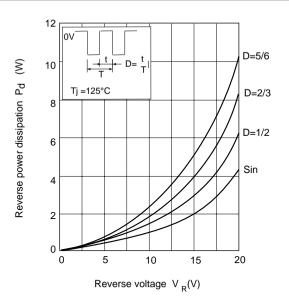


Fig.5 Reverse power dissipation Vs. Reverse voltage

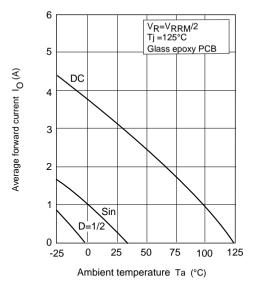
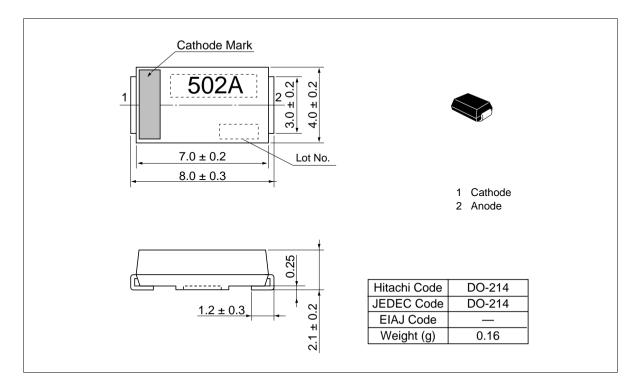


Fig.7 Average forward current Vs. Ambient temperature

# **Package Dimensions**

Unit: mm



#### **Cautions**

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